CSD19538Q2 100V N-Channel NexFET™ Power MOSFET

1 Features

- Ultra-low Q_g and Q_{gd}
- Low-thermal resistance
- Avalanche rated
- Lead free
- RoHS compliant
- Halogen free
- SON 2mm × 2mm plastic package

2 Applications

- Power over ethernet (PoE)
- Power sourcing equipment (PSE)
- Motor control

Description

This 100V, 49mΩ, SON 2mm × 2mm NexFET™ power MOSFET is designed to minimize losses in power conversion applications.

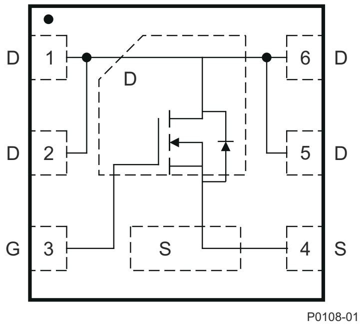


Figure 3-1. Top View

Product Summary

T_A = 25°C		TYPICAL VALUE		UNIT
V_{DS}	Drain-to-Source Voltage	100		V
Q_g	Gate Charge Total (10V)	4.3		nC
Q_{gd}	Gate Charge Gate-to-Drain	0.8		nC
$R_{DS(on)}$	Drain-to-Source On Resistance	V_{GS} = 6V	58	mΩ
		V_{GS} = 10V	49	
$V_{GS(th)}$	Threshold Voltage	3.2		V

Device Information(1)

DEVICE	QTY	MEDIA	PACKAGE	SHIP
CSD19538Q2	3000	7 Inch Reel	SON 2.00mm x 2.00mm Plastic Package	Tape and Reel
CSD19538Q2T	250			
CSD19538Q2R	10,000	13 Inch Reel		

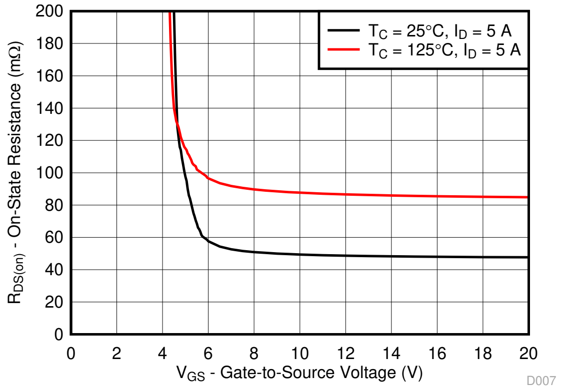
(1) For all available packages, see the orderable addendum at the end of the data sheet.

Absolute Maximum Ratings

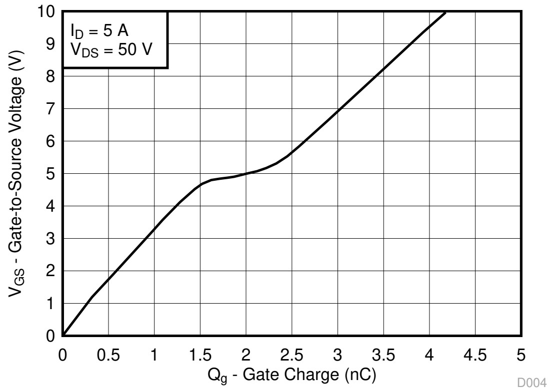
T_A = 25°C		VALUE	UNIT
V_{DS}	Drain-to-Source Voltage	100	V
V_{GS}	Gate-to-Source Voltage	±20	V
I_D	Continuous Drain Current (Package Limited)	14.4	A
	Continuous Drain Current (Silicon Limited), T_C = 25°C	13.1	
	Continuous Drain Current(1)	4.6	
I_{DM}	Pulsed Drain Current(2)	34.4	A
P_D	Power Dissipation(1)	2.5	W
	Power Dissipation, T_C = 25°C	20.2	
T_J, T_{stg}	Operating Junction Temperature, Storage Temperature	–55 to 150	°C
E_{AS}	Avalanche Energy, Single Pulse I_D = 12.6A, L = 0.1mH, R_G = 25Ω	8	mJ

(1) Typical $R_{\theta JA}$ = 50°C/W on a 1 inch^2, 2oz Cu pad on a 0.06 inch thick FR4 PCB.

(2) Max $R_{\theta JC}$ = 6.2°C/W, pulse duration ≤ 100μs, duty cycle ≤ 1%.



$R_{DS(on)}$ vs V_{GS}



Gate Charge

Table of Contents

1 Features............1
2 Applications............1
3 Specifications............3
  3.1 Electrical Characteristics............3
  3.2 Thermal Information............3
  3.3 Typical MOSFET Characteristics............4
4 Device and Documentation Support............7
  4.1 Third-Party Products Disclaimer............7
  4.2 Receiving Notification of Documentation Updates............7
  4.3 Support Resources............7
  4.4 Trademarks............7
  4.5 Electrostatic Discharge Caution............7
  4.6 Glossary............7
5 Revision History............7
6 Mechanical, Packaging, and Orderable Information............8

3 Specifications

3.1 Electrical Characteristics

T_A = 25°C (unless otherwise stated)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC CHARACTERISTICS						
BV_{DSS}	Drain-to-source voltage	V_{GS} = 0V, I_D = 250μA	100			V
I_{DSS}	Drain-to-source leakage current	V_{GS} = 0V, V_{DS} = 80V			1	μA
I_{GSS}	Gate-to-source leakage current	V_{DS} = 0V, V_{GS} = 20V			100	nA
$V_{GS(th)}$	Gate-to-source threshold voltage	V_{DS} = V_{GS}, I_D = 250μA	2.8	3.2	3.8	V
$R_{DS(on)}$	Drain-to-source on resistance	V_{GS} = 6V, I_D = 5A		58	72	mΩ
		V_{GS} = 10V, I_D = 5A		49	59	
g_{fs}	Transconductance	V_{DS} = 10V, I_D = 5A		19		S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input capacitance	V_{GS} = 0V, V_{DS} = 50V, f = 1MHz		349	454	pF
C_{oss}	Output capacitance			69	90	pF
C_{rss}	Reverse transfer capacitance			12.6	16.4	pF
R_G	Series gate resistance			4.6	9.2	Ω
Q_g	Gate charge total (10V)	V_{DS} = 50V, I_D = 5A		4.3	5.6	nC
Q_{gd}	Gate charge gate-to-drain			0.8		nC
Q_{gs}	Gate charge gate-to-source			1.6		nC
$Q_{g(th)}$	Gate charge at V_{th}			1.0		nC
Q_{oss}	Output charge	V_{DS} = 50V, V_{GS} = 0V		12.3		nC
$t_{d(on)}$	Turnon delay time	V_{DS} = 50V, V_{GS} = 10V, I_{DS} = 5A, R_G = 0Ω		5		ns
t_r	Rise time			3		ns
$t_{d(off)}$	Turnoff delay time			7		ns
t_f	Fall time			2		ns
DIODE CHARACTERISTICS						
V_{SD}	Diode forward voltage	I_{SD} = 5A, V_{GS} = 0V		0.85	1.0	V
Q_{rr}	Reverse recovery charge	V_{DS}= 50V, I_F = 5A, di/dt = 300A/μs		94		nC
t_{rr}	Reverse recovery time			32		ns

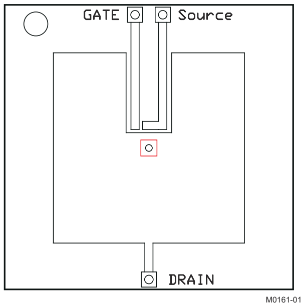
3.2 Thermal Information

T_A = 25°C (unless otherwise stated)

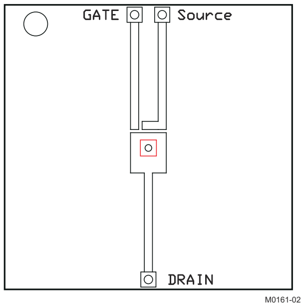
THERMAL METRIC		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction-to-case thermal resistance(1)			6.2	°C/W
$R_{\theta JA}$	Junction-to-ambient thermal resistance(1) (2)			65	°C/W

(1) $R_{\theta JC}$ is determined with the device mounted on a 1in^2 (6.45cm^2), 2oz (0.071mm) thick Cu pad on a 1.5in × 1.5in (3.81cm × 3.81cm), 0.06in (1.52mm) thick FR4 PCB. $R_{\theta JC}$ is specified by design, whereas $R_{\theta JA}$ is determined by the user's board design.

(2) Device mounted on FR4 material with 1in^2 (6.45cm^2), 2oz (0.071mm) thick Cu.



Max $R_{\theta JA}$ = 65°C/W when mounted on $1 in^2$ ($6.45 cm^2$) of 2oz (0.071mm) thick Cu.



Max $R_{\theta JA}$ = 250°C/W when mounted on a minimum pad area of 2oz (0.071mm) thick Cu.

3.3 Typical MOSFET Characteristics

T_A = 25°C (unless otherwise stated)

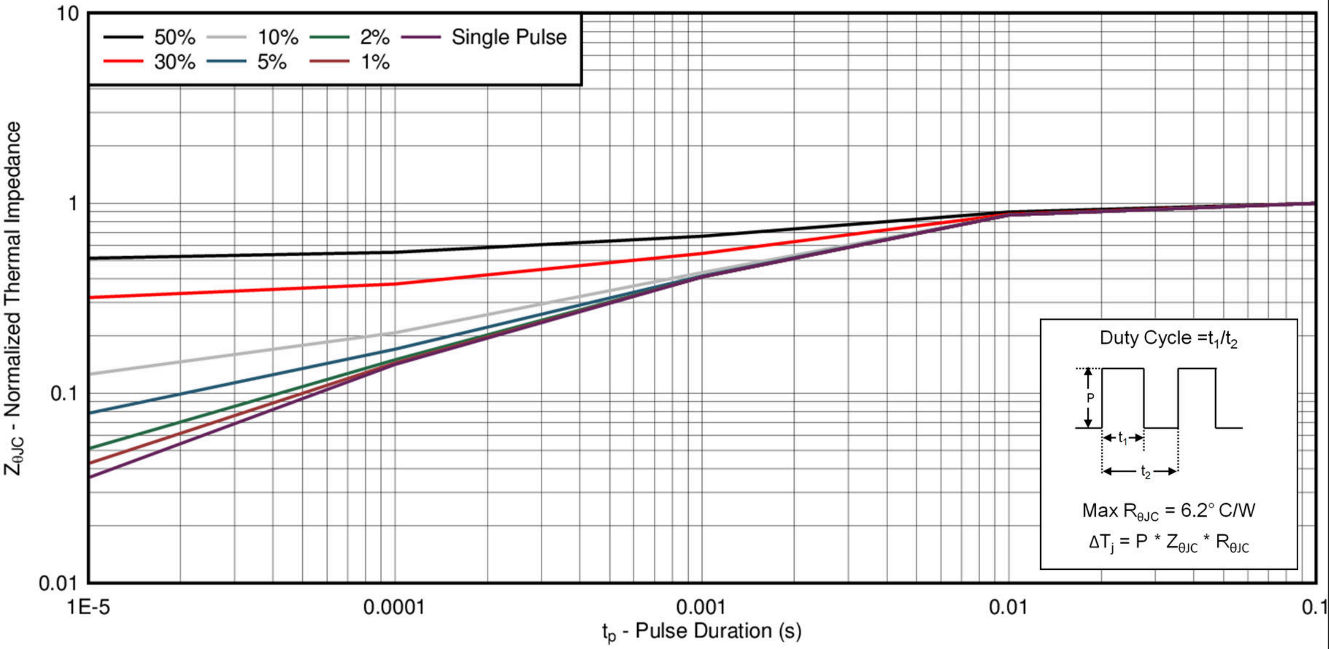


Figure 3-1. Transient Thermal Impedance

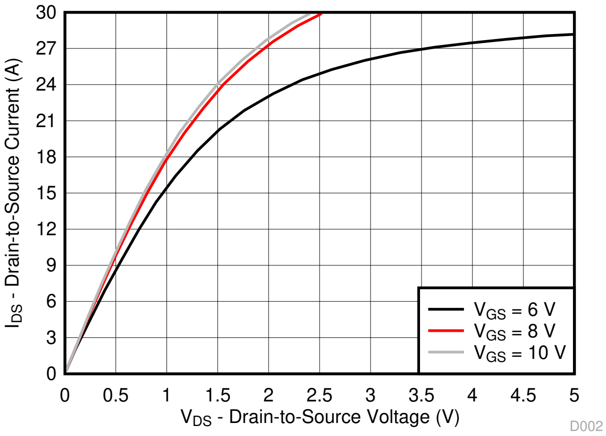
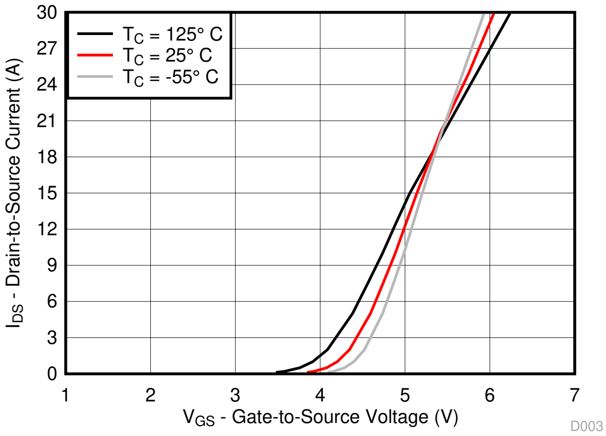
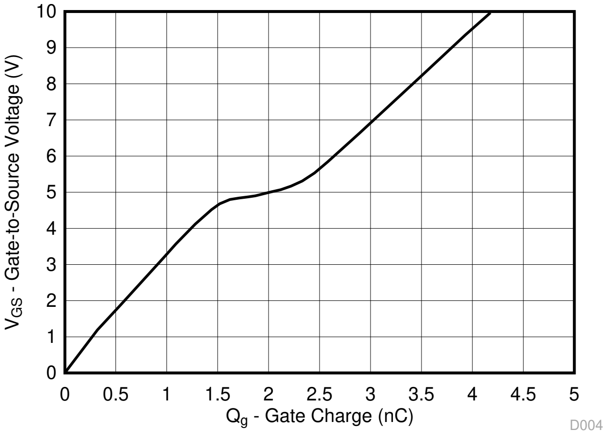


Figure 3-2. Saturation Characteristics



V_{DS} = 5V

Figure 3-3. Transfer Characteristics



I_D = 5A V_{DS} = 50V

Figure 3-4. Gate Charge

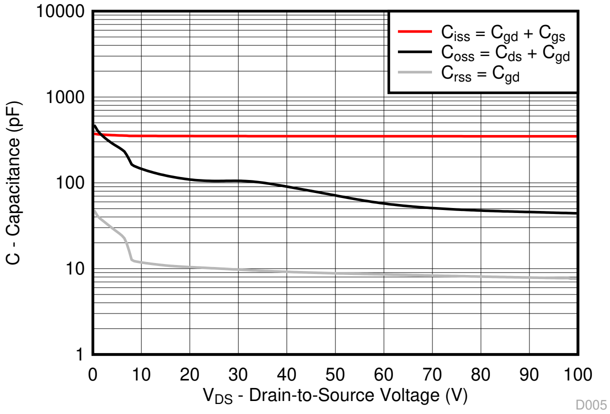
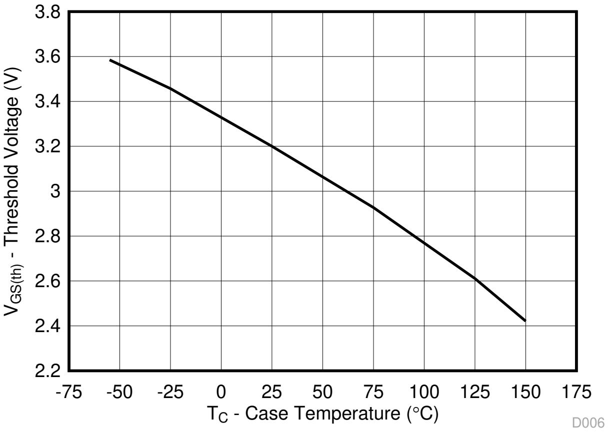


Figure 3-5. Capacitance



I_D = 250µA

Figure 3-6. Threshold Voltage vs Temperature

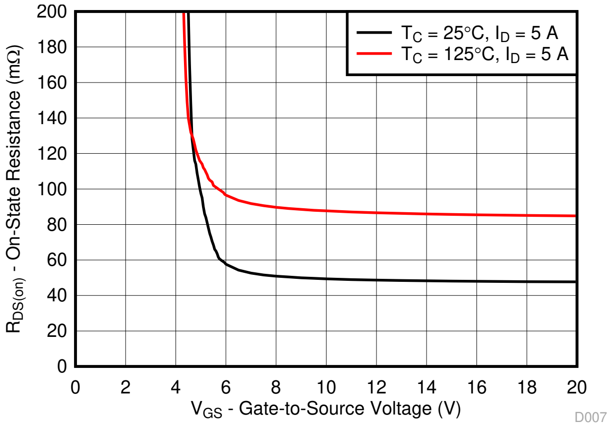
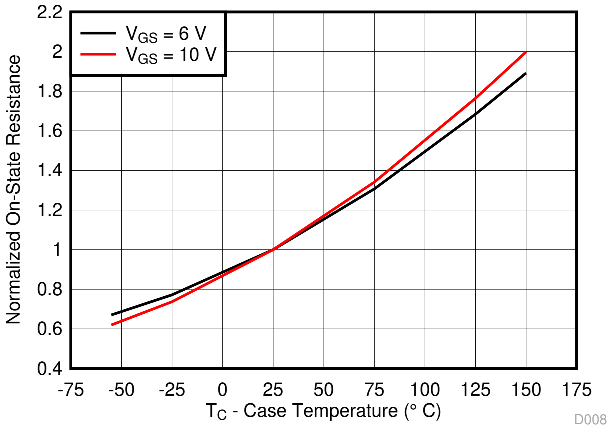


Figure 3-7. On-State Resistance vs Gate-to-Source Voltage



I_D = 5A

Figure 3-8. Normalized On-State Resistance vs Temperature

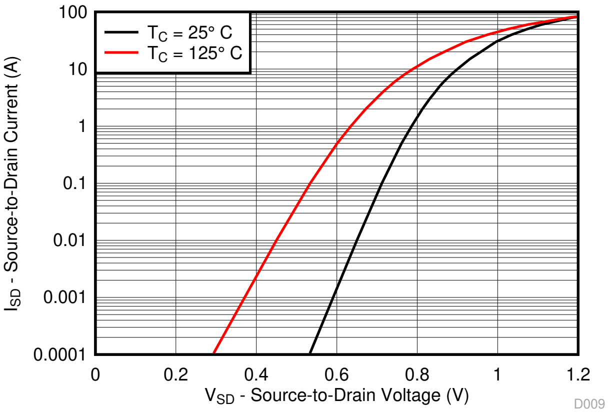
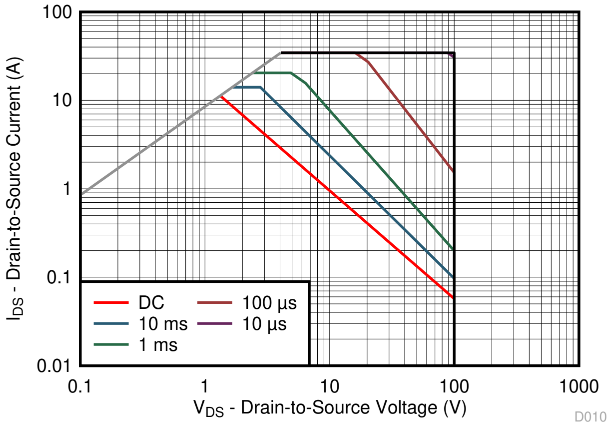


Figure 3-9. Typical Diode Forward Voltage



Single pulse, max $R_{\theta JC}$ = 6.2°C/W

Figure 3-10. Maximum Safe Operating Area

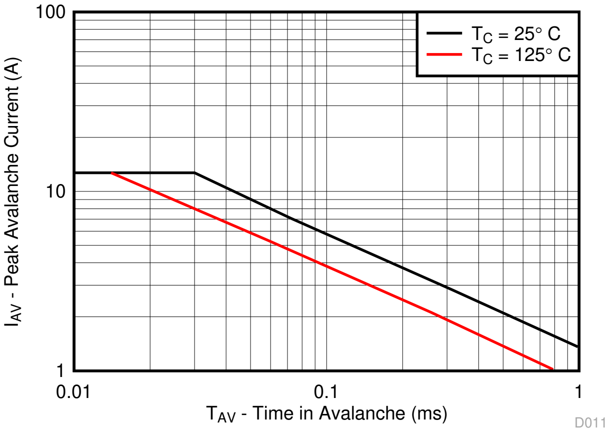


Figure 3-11. Single Pulse Unclamped Inductive Switching

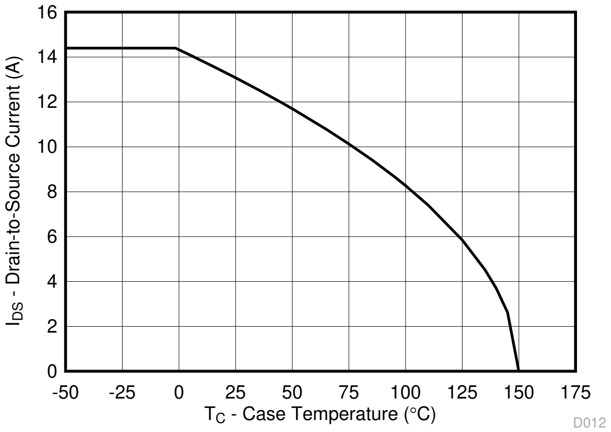


Figure 3-12. Maximum Drain Current vs Temperature

4 Device and Documentation Support

4.1 Third-Party Products Disclaimer

TI'S PUBLICATION OF INFORMATION REGARDING THIRD-PARTY PRODUCTS OR SERVICES DOES NOT CONSTITUTE AN ENDORSEMENT REGARDING THE SUITABILITY OF SUCH PRODUCTS OR SERVICES OR A WARRANTY, REPRESENTATION OR ENDORSEMENT OF SUCH PRODUCTS OR SERVICES, EITHER ALONE OR IN COMBINATION WITH ANY TI PRODUCT OR SERVICE.

4.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

4.3 Support Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

4.4 Trademarks

NexFET™ and TI E2E™ are trademarks of Texas Instruments.
All trademarks are the property of their respective owners.

4.5 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

4.6 Glossary

TI Glossary	This glossary lists and explains terms, acronyms, and definitions.

5 Revision History

Changes from Revision A (January 2017) to Revision B (March 2024) **Page**

- Updated the numbering format for tables, figures, and cross-references throughout the document................. 1

Changes from Revision * (July 2016) to Revision A (January 2017) **Page**

- Changed test voltage V_{DS} from 100V : to 50V in Figure 3-2 curve.. 1
- Changed test voltage V_{DS} from 100V : to 50V in Figure 3-4 4

6 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGE OPTION ADDENDUM

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
CSD19538Q2	Active	Production	WSON (DQK) | 6	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 150	1958
CSD19538Q2.B	Active	Production	WSON (DQK) | 6	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 150	1958
CSD19538Q2G4.B	Active	Production	WSON (DQK) | 6	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 150	1958
CSD19538Q2R	Active	Production	WSON (DQK) | 6	10000 | JUMBO T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 150	1958
CSD19538Q2R.B	Active	Production	WSON (DQK) | 6	10000 | JUMBO T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 150	1958
CSD19538Q2T	Active	Production	WSON (DQK) | 6	250 | SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 150	1958
CSD19538Q2T.B	Active	Production	WSON (DQK) | 6	250 | SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 150	1958

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

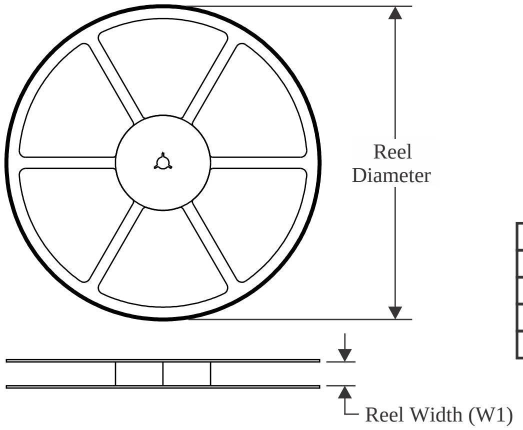
Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

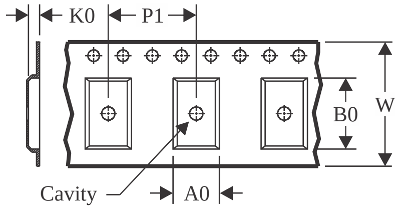
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

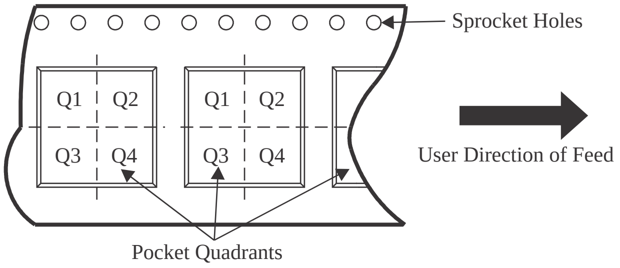


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

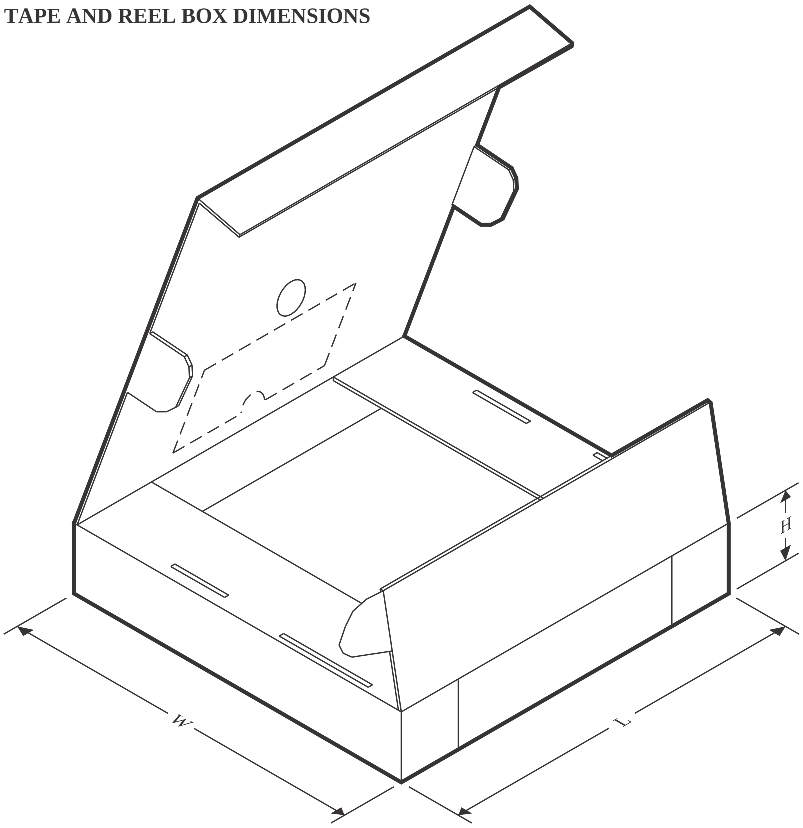
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD19538Q2	WSON	DQK	6	3000	180.0	9.5	2.3	2.3	1.0	4.0	8.0	Q1
CSD19538Q2T	WSON	DQK	6	250	180.0	9.5	2.3	2.3	1.0	4.0	8.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD19538Q2	WSON	DQK	6	3000	189.0	185.0	36.0
CSD19538Q2T	WSON	DQK	6	250	189.0	185.0	36.0

GENERIC PACKAGE VIEW

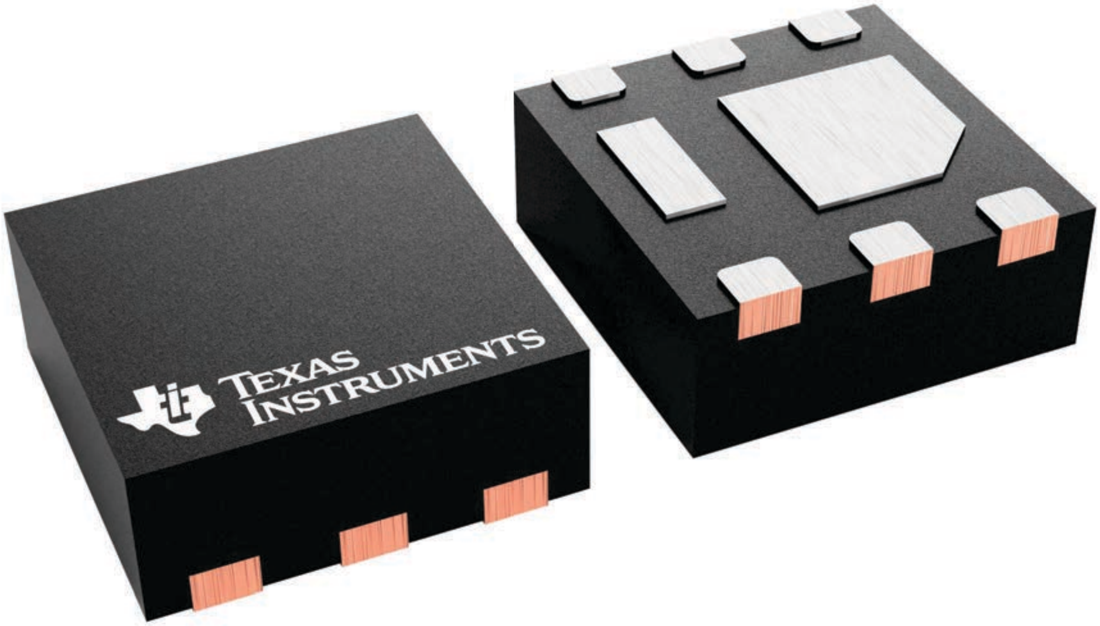
DQK 6

WSON - 0.8 mm max height

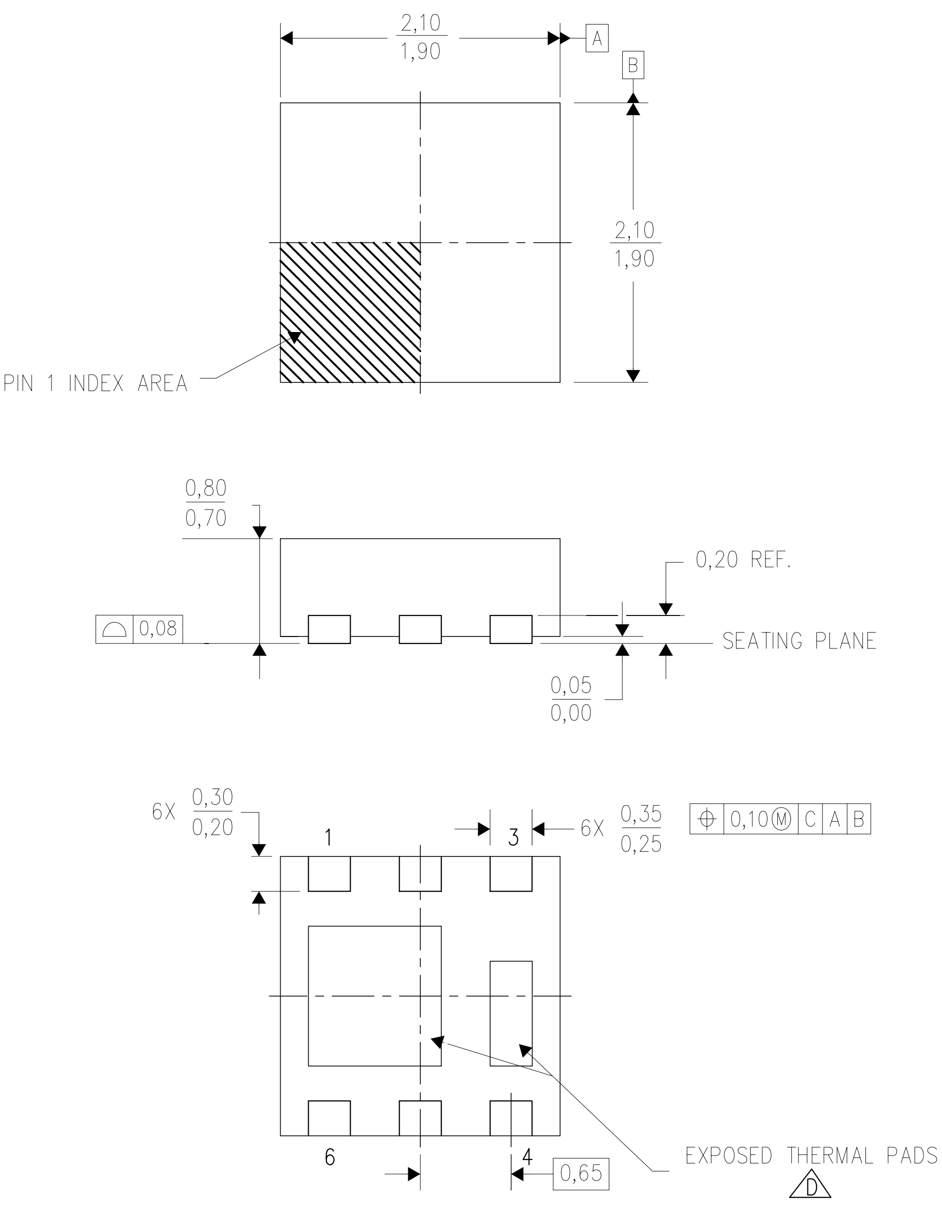
2 x 2, 0.65 mm pitch

PLASTIC SMALL OUTLINE - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



DQK (S-PWSON-N6) PLASTIC SMALL OUTLINE NO-LEAD



4210192/B 01/10

NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. Small Outline No–Lead (SON) package configuration.
D. The package thermal pads must be soldered to the board for thermal and mechanical performance.

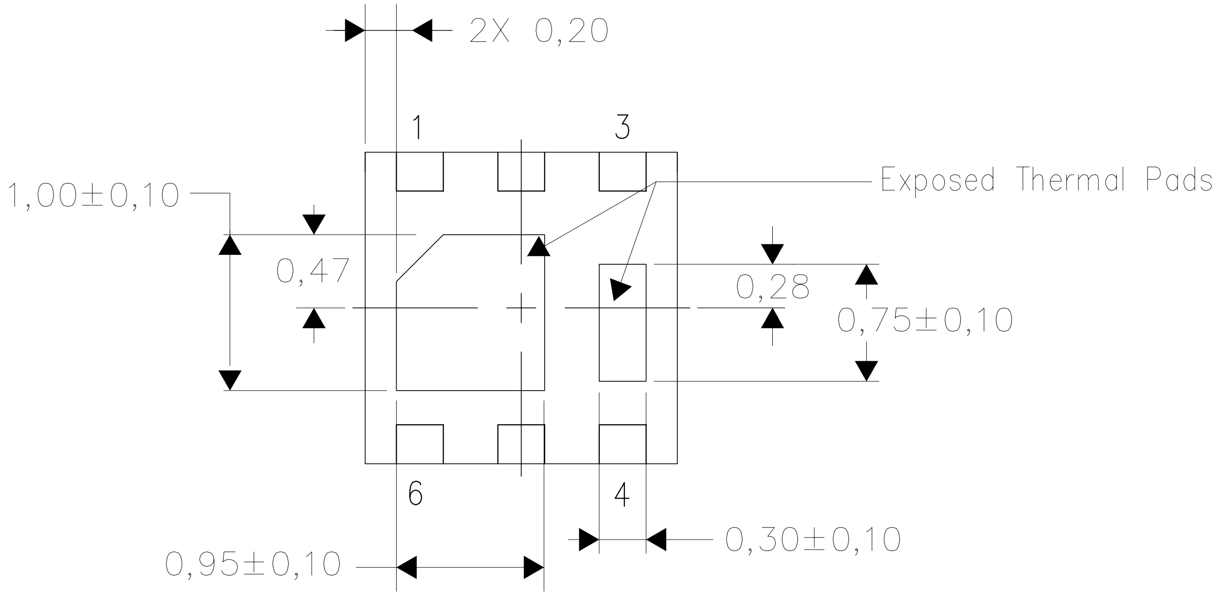
THERMAL PAD MECHANICAL DATA

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No–Lead (QFN) package and its advantages, refer to Application Report, Quad Flatpack No–Lead Logic Packages, Texas Instruments Literature No. SCBA017. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Bottom View

NOTE: All linear dimensions are in millimeters

Exposed Thermal Pad Dimensions

IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES “AS IS” AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you fully indemnify TI and its representatives against any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI’s products are provided subject to TI’s Terms of Sale, TI’s General Quality Guidelines, or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI’s provision of these resources does not expand or otherwise alter TI’s applicable warranties or warranty disclaimers for TI products. Unless TI explicitly designates a product as custom or customer-specified, TI products are standard, catalog, general purpose devices.

TI objects to and rejects any additional or different terms you may propose.

Copyright © 2025, Texas Instruments Incorporated

Last updated 10/2025